

50V DUAL NPN LOW SATURATION SWITCHING TRANSISTOR IN SOT26

Features

- BV_{CEO} > 50V
- I_C = 1A High Continuous Current
- High Gain
- R_{SAT} = 160mΩ for Low Equivalent On Resistance
- Low Saturation Voltage V_{CE(sat)} < -270mV @ 1A
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

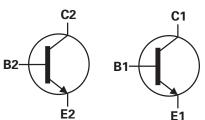
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.015 grams (approximate)

Applications

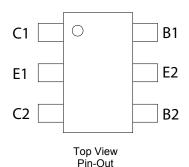
- LCD Backlighting Inverter Circuits
- · Boost Functions in DC-DC Converters







Device Symbol



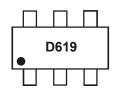
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD09N50DE6TA	AEC-Q101	D619	7	8	3,000
ZTD09N50DE6QTA	Automotive	D619	7	8	3.000

Notes:

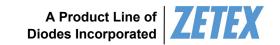
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/ for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

Marking Information



D619 = Product Type Marking Code





Maximum Ratings - Q1 & Q2 Common (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Current	Ісм	2	Α
Base current	Ι _Β	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Notes 6 & 10)		0.7 5.6		
	(Notes 7 & 10)		0.9 7.2	W mW/°C	
Power Dissipation Linear Derating Factor	(Notes 7 & 11)	P _D	1.1 8.8		
	(Notes 8 & 10)		1.1 8.8		
	(Notes 9 & 10)		1.7 13.6		
	(Notes 6 & 10)		179	OCAN	
	(Notes 7 & 10)		139		
Thermal Resistance, Junction to Ambient	(Notes 7 & 11)	$R_{ hetaJA}$	113		
	(Notes 8 & 10)		113	°C/W	
	(Notes 9 & 10)		73		
Thermal Resistance, Junction to Lead	(Note 12)	$R_{ hetaJL}$	95.50		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

Notes:

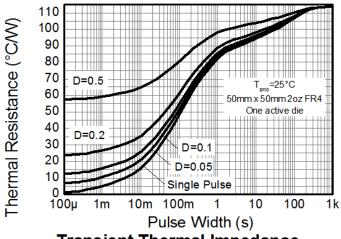
- 6. For a device surface mounted on 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured b. For a device surface mounted on 15mm x 15mm FR4 PCB with high coverage of single when operating in a steady-state condition.
 7. Same as note (6), except the device is surface mounted on 25mm x 25mm 1oz copper.
 8. Same as note (6), except the device is surface mounted on 50mm x 50mm 2oz copper.
 9. Same as note (8), except the device is measured at t < 5 seconds.
 10. For device with one active die, both collectors attached to a common heatsink.
 11. For device with the active dies running at equal power, solid heatsink 50% to each collection.

- 11. For device with two active dice running at equal power, split heatsink 50% to each collector.
- 12. Thermal resistance from junction to solder-point (at the end of the collector lead).

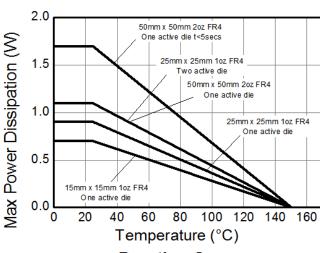




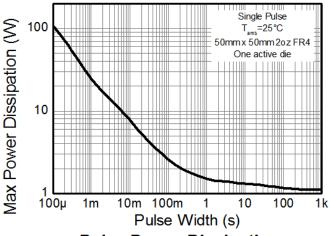
Thermal Characteristics and Derating Information



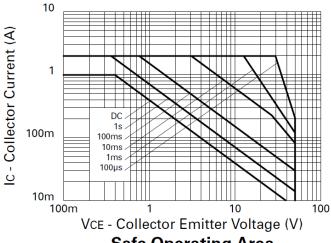
Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation



Safe Operating Area





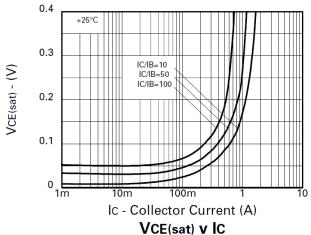
Electrical Characteristics - Q1 & Q2 common (@TA = +25°C, unless otherwise specified.)

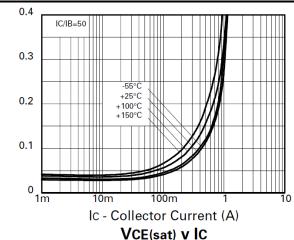
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50			V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 13)	BV _{CEO}	50			٧	I _C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7			V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}			10	nA	V _{CB} = 40V
Collector-Emitter Cutoff Current	I _{CES}			10	nA	V _{CES} = 40V
Emitter Cutoff Current	I _{EBO}			10	nA	V _{EB} = 5.6V
DC Current Gain (Note 13)	h _{FE}	200 300 200 75 20	420 450 350 130 60			$\begin{split} &I_{C} = 10\text{mA}, \ V_{CE} = 2\text{V} \\ &I_{C} = 100\text{mA}, \ V_{CE} = 2\text{V} \\ &I_{C} = 500\text{mA}, \ V_{CE} = 2\text{V} \\ &I_{C} = 1\text{A}, \ V_{CE} = 2\text{V} \\ &I_{C} = 1.5\text{A}, \ V_{CE} = 2\text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 13)	V _{CE(sat)}		24 60 120 160	35 80 200 270	mV	$I_C = 100$ mA, $I_B = 10$ mA $I_C = 250$ mA, $I_B = 10$ mA $I_C = 500$ mA, $I_B = 10$ mA $I_C = 1$ A, $I_B = 50$ mA
Base-Emitter Saturation Voltage (Note 13)	$V_{BE(sat)}$		940	1100	mV	I _C = 1A, I _B = 50mA
Base-Emitter Turn-On Voltage (Note 13)	$V_{BE(on)}$		850	1100	mV	I _C = 1A, V _{CE} = 2V
Output Capacitance	C_obo		10		pF	V _{CB} = 10V. f = 1MHz
Current Gain-Bandwidth Product	f _T		215		MHz	$V_{CE} = 10V, I_{C} = 50mA$ f = 100MHz
Turn-On Time	t _{on}		150		ns	V _{CC} = 10V, I _C = 1A
Turn-Off Time	$t_{\rm off}$		425		ns	I _{B1} = I _{B2} = 100mA

Notes: 13. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



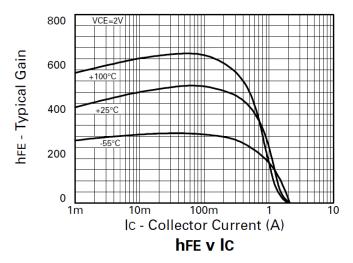


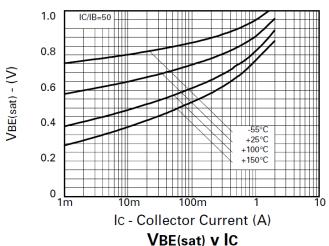


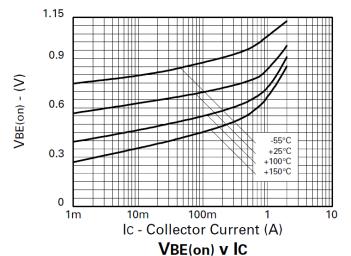


VCE(sat) - (V)







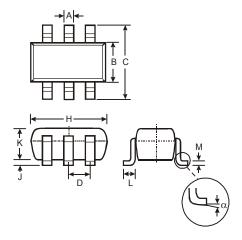






Package Outline Dimensions

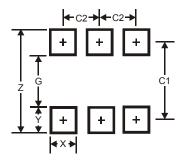
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT26					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D	_	_	0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
K	1.00	1.30	1.10		
L	0.35	0.55	0.40		
M	0.10	0.20	0.15		
α	0°	8°	_		
All Dimensions in mm					

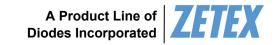
Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95





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